



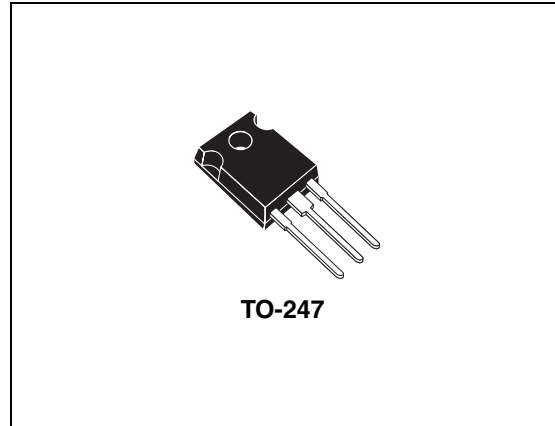
STW45NM60

N-channel 650V @ Tjmax - 0.09Ω - 45A - TO-247
MDmesh™ Power MOSFET

General features

Type	V _{DSS} (@T _{jmax})	R _{DS(on)}	I _D
STW45NM60	650V	< 0.11Ω	45A

- High dv/dt and avalanche capabilities
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Tight process control and high manufacturing yields



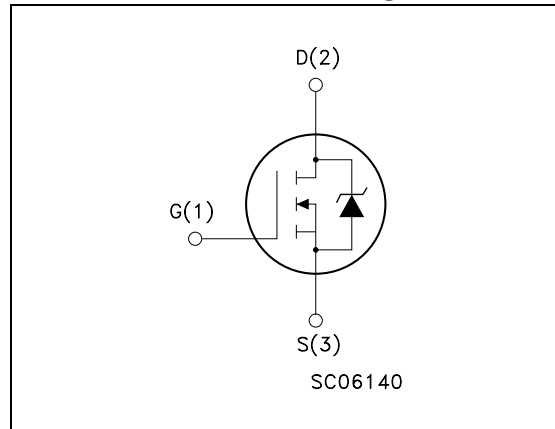
Description

The MDmesh™ is a new revolutionary Power MOSFET technology that associates the multiple drain process with the Company's PowerMESH™ horizontal layout. The resulting product has an outstanding low on-resistance, impressively high dv/dt and excellent avalanche characteristics. The adoption of the Company's proprietary strip technique yields overall dynamic performance that is significantly better than that of similar competitor's products.

Applications

- Switching application

Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STW45NM60	W45NM60	TO-247	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate- source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	45	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	28	A
$I_{DM}^{(1)}$	Drain current (pulsed)	180	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	417	W
	Derating factor	3.33	W/°C
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	-65 to 150	°C
T_j	Max. operating junction temperature	150	°C

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 45\text{A}$, $di/dt \leq 400\text{A}/\mu\text{s}$, $V_{DD} \leq 80\% V_{(BR)DSS}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.3	°C/W
$R_{thj-amb}$	Thermal resistance junction-amb	30	°C/W
T_l	Maximum lead temperature for soldering purpose	300	°C

Table 3. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	15	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 35\text{V}$)	850	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	600			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}, T_C = 125^{\circ}C$			10 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 30V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 22.5A$		0.09	0.11	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}, I_D = 22.5A$		15		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		3800 1250 80		pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 480V$		340		pF
R_G	Gate input resistance	$f=1 \text{ MHz}$ Gate DC Bias = 0 test signal level = 20mV open drain		1.4		Ω
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 400V, I_D = 45A,$ $V_{GS} = 10V$ <i>Figure 14</i>		96 31 43	134	nC nC nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250V, I_D = 22.5A$ $R_G = 4.7\Omega, V_{GS} = 10V$ <i>Figure 13</i>		30		ns
t_r	Rise time			20		ns
$t_{r(Voff)}$	Off-voltage rise time	$V_{DD} = 400V, I_D = 45A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ <i>Figure 13</i>		16		ns
t_f	Fall time			23		ns
t_c	Cross-over time			40		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				45	A
I_{SDM}	Source-drain current (pulsed)				180	A
$V_{SD}^{(1)}$	Forward on voltage	$I_{SD} = 45A, V_{GS} = 0$			1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 45A,$ $di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 25^\circ C$ <i>Figure 15</i>		508		ns
Q_{rr}	Reverse recovery charge			10		μC
I_{RRM}	Reverse recovery current			40		A
t_{rr}	Reverse recovery time	$I_{SD} = 45A,$ $di/dt = 100A/\mu s,$ $V_{DD} = 100V, T_j = 150^\circ C$ <i>Figure 15</i>		650		ns
Q_{rr}	Reverse recovery charge			14		μC
I_{RRM}	Reverse recovery current			43		A

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

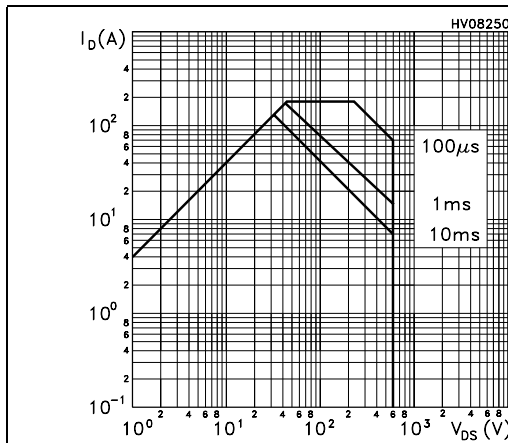


Figure 2. Thermal impedance

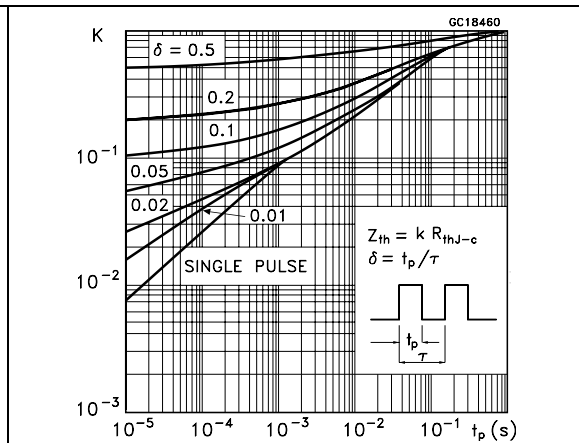


Figure 3. Output characteristics

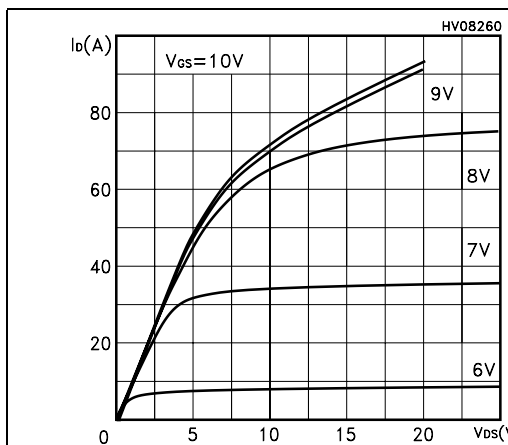


Figure 4. Transfer characteristics

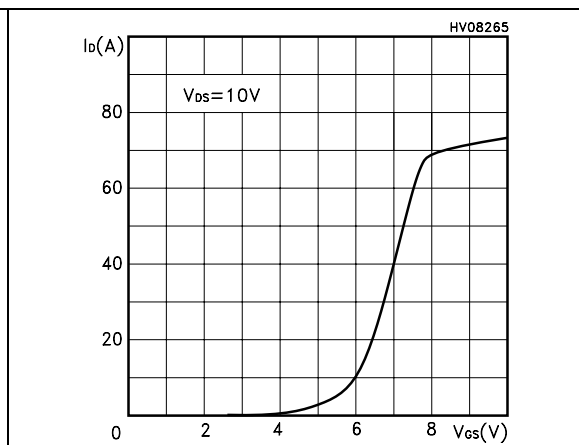


Figure 5. Transconductance

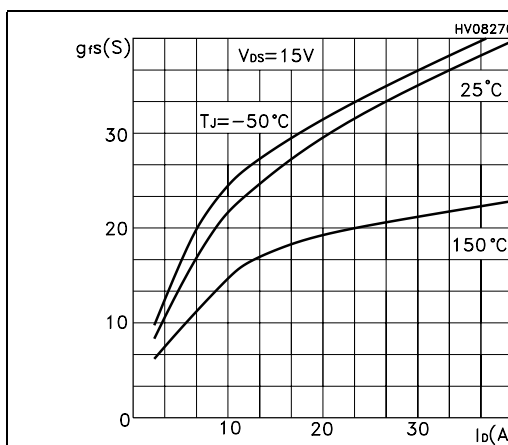


Figure 6. Static-drain source on resistance

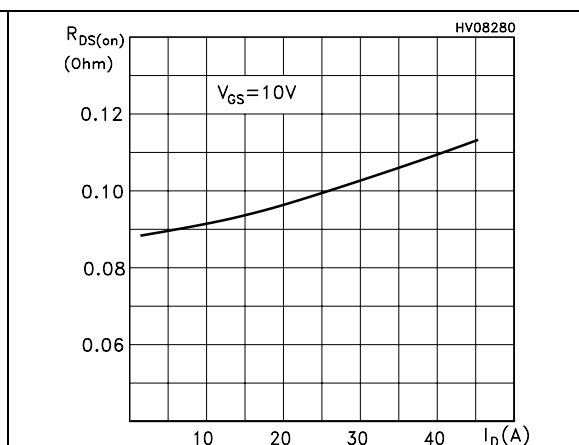


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

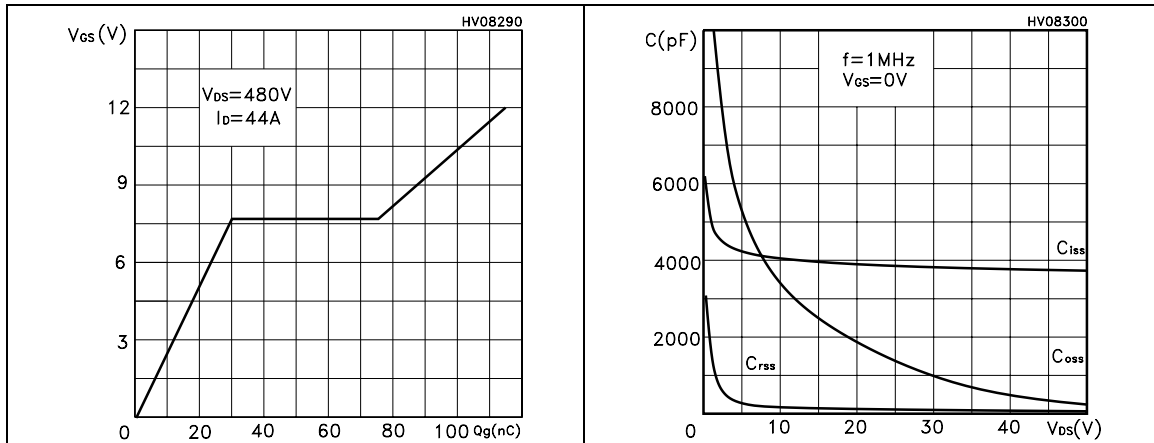


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

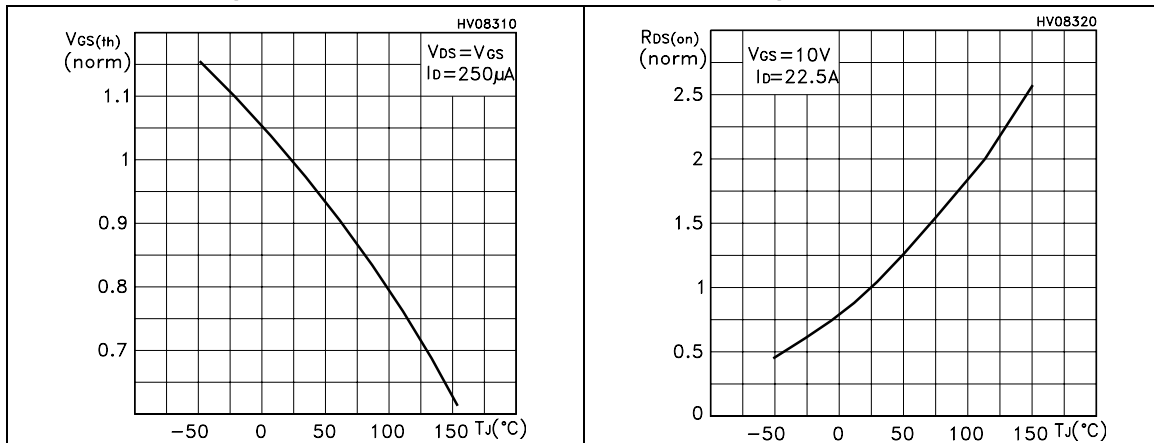
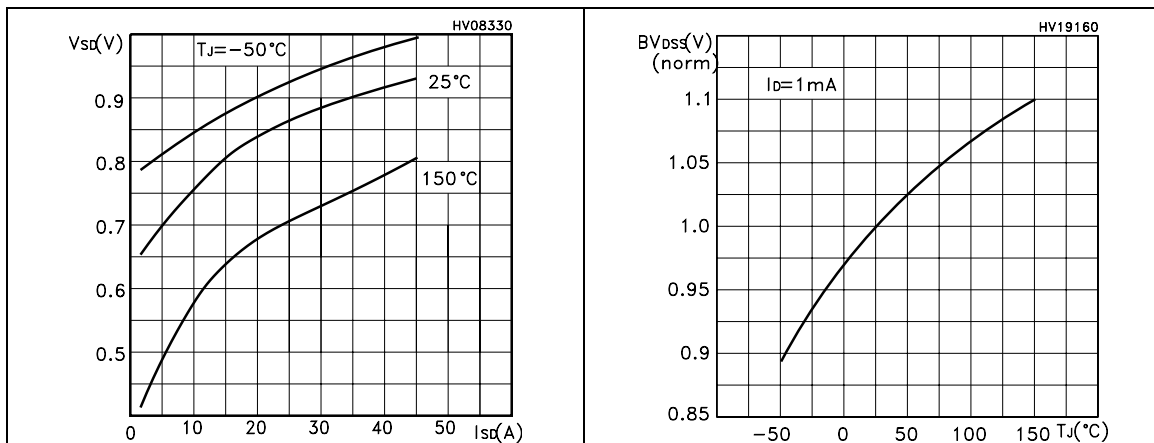


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized BV_{DSS} vs temperature



3 Test circuit

Figure 13. Switching times test circuit for resistive load

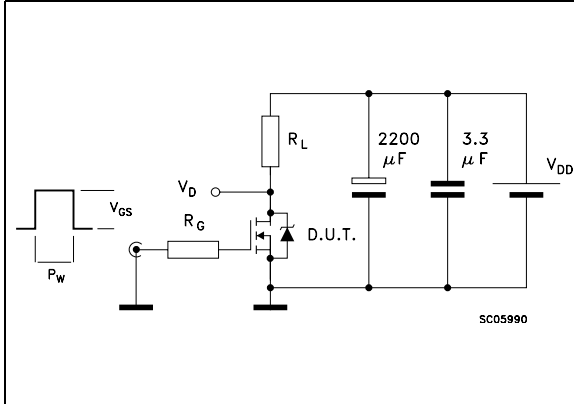


Figure 14. Gate charge test circuit

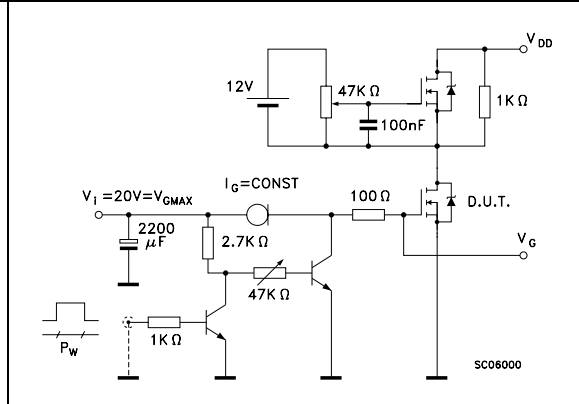


Figure 15. Test circuit for inductive load switching and diode recovery times

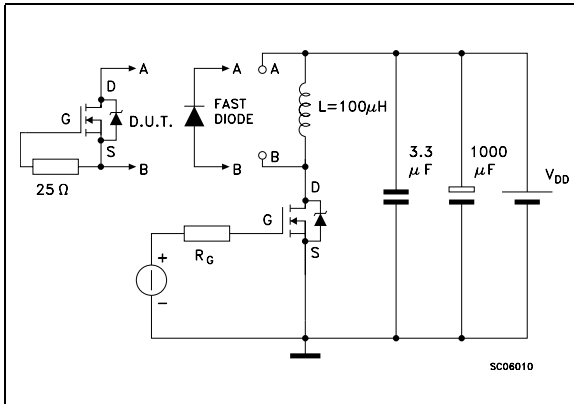


Figure 16. Unclamped inductive load test circuit

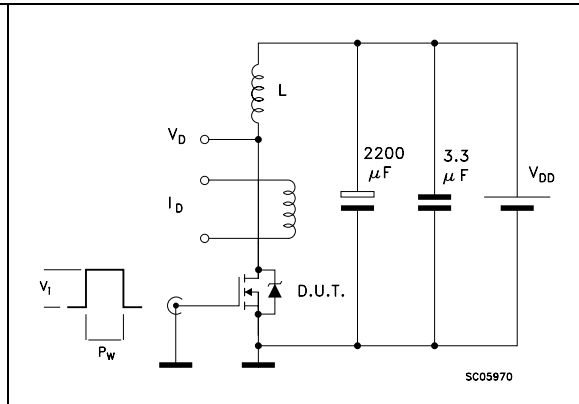


Figure 17. Unclamped inductive waveform

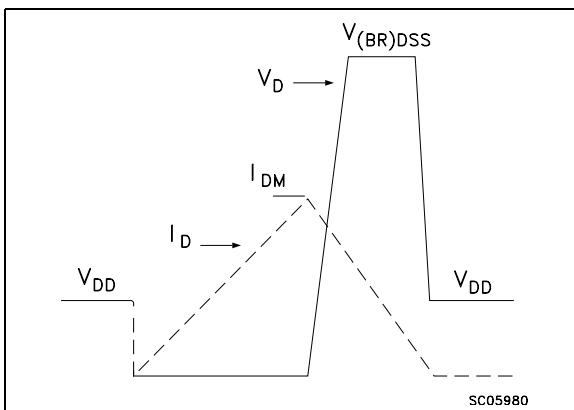
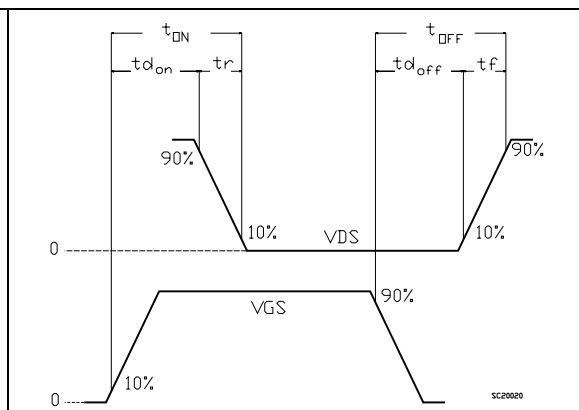


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

5 Revision history

Table 8. Revision history

Date	Revision	Changes
05-Mar-2005	5	Complete document with curves
16-May-2006	6	The document has been reformatted
18-Dec-2006	7	Updates curves: Figure 1. , Figure 4. and Figure 6.

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